



SEMICONDUCTOR

SS5817T THRU SS5819T

SURFACE MOUNT SCHOTTKY BARRIER RECTIFIER

Reverse Voltage - 20 to 40 Volts

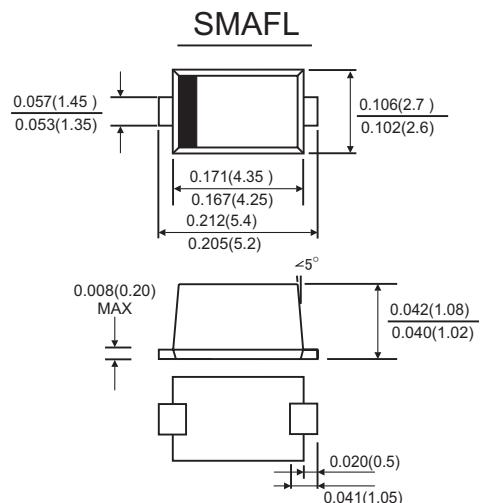
Forward Current - 1.0Ampere

FEATURES

- Plastic package has Underwriters Laboratory Flammability Classification 94V-0
- Metal silicon junction ,majority carrier conduction
- For surface mount applications
- Guard ring for overvoltage protection
- Low power loss ,high efficiency
- High current capability ,Low forward voltage drop
- High surge capability
- For use in low voltage ,high frequency inverters, free wheeling ,and polarity protection applications
- High temperature soldering guaranteed:260°C/10 seconds at terminals
- Component in accordance to RoHS 2011/65/EU

MECHANICAL DATA

- Case: SMAFL molded plastic body
- TERMINALS: Solder Plated, solderable per MIL-STD-750,method 2026
- Polarity: Color band denotes cathode end



Dimensions in inches and (millimeters)

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

(Ratings at 25°C ambient temperature unless otherwise specified ,Single phase ,half wave ,resistive or inductive load. For capacitive load,derate by 20%.)

	Symbols	SS 5817T	SS 5818T	SS 5819T	Units
Maximum repetitive peak reverse voltage	V _{RRM}	20	30	40	Volts
Maximum RMS voltage	V _{RMS}	14	21	28	Volts
Maximum DC blocking voltage	V _{DC}	20	30	40	Volts
Maximum non-repetitive peak reverse voltage	V _{RSM}	24	36	48	Volts
Maximum average forward rectified current	I _(AV)		1.0		Amp
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC method)	I _{FSM}		25.0		Amps
Maximum instantaneous forward voltage at 1.0 A(note 1)	V _F	0.450	0.550	0.600	Volts
Maximum instantaneous forward voltage at 3.0 A(note 1)	V _F	0.750	0.875	0.900	Volts
Maximum instantaneous reverse current at rated DC blocking voltage(Note 1)	I _R <small>T_A=25°C</small> <small>T_A=100°C</small>		0.1		mA
			5.0		
Typical junction capacitance(Note 3)	C _J		110.0		pF
Typical thermal resistance (Note 2)	R _{θJA} R _{θJL}		115 28.0		°C/W
Operating junction and storage temperature range	T _J T _{STG}		-65 to +150		°C

Notes: 1.Pulse test: 300 μs pulse width,1% duty cycle

2.Thermal resistance (from junction to ambient)Vertical P.C.B. mounted , with 1.5X1.5"(38X38mm)copper pads

3.Measured at 1.0MHz and reverse voltage of 4.0 volts

RATINGS AND CHARACTERISTIC CURVES SS5817T THRU SS5819T

FIG.1-FORWARD CURRENT DERATING CURVE

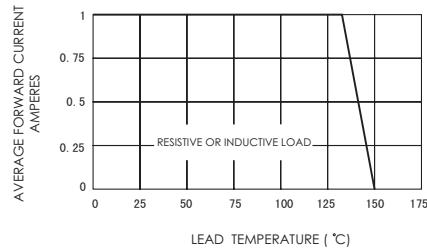


FIG.3-TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

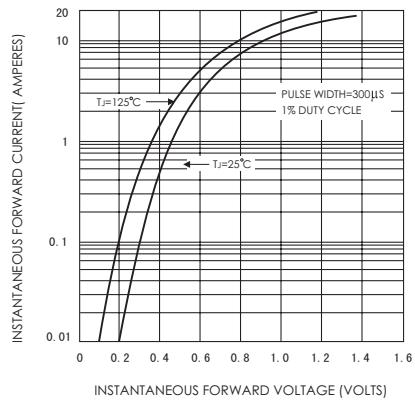


FIG.5-TYPICAL JUNCTION CAPACITANCE

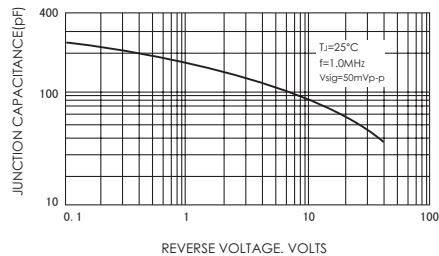


FIG.2-MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

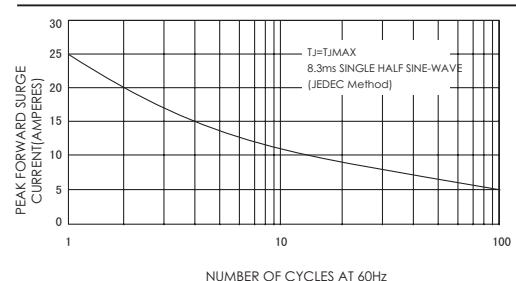


FIG.4-TYPICAL REVERSE CHARACTERISTICS

